

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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DDTD (LO-R1)

Max

0.40

1.35

2.20

0.40

1.40

2.20

0.10

1.00

0.40

0.18

8°

NPN PRE-BIASED 500 mA SURFACE MOUNT TRANSISTOR

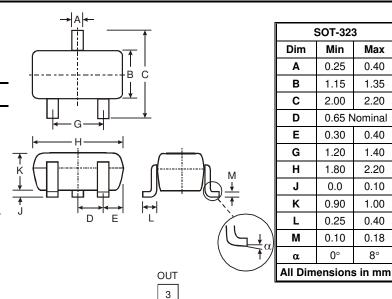
Features

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDTB)
- **Built-In Biasing Resistors**
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device, Note 3 and 4

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Table Below & Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)

P/N	R1 (NOM)	R2 (NOM)	MARKING
DDTD122LU	0.22KΩ	10ΚΩ	N75
DDTD142JU	0.47ΚΩ	10KΩ	N76
DDTD122TU	0.22KΩ	OPEN	N77
DDTD142TU	0.47ΚΩ	OPEN	N78



Schematic and Pin Configuration

1

: R2

2

GND(0)

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Supply Voltage, (3) to (2)		V_{CC}	50	V
Input Voltage, (1) to (2)	DDTD122LU DDTD142JU	V _{IN}	-5 to +6 -5 to +6	V
Input Voltage, (2) to (1)	DDTD122TU DDTD142TU	V _{EBO (MAX)}	5	V
Output Current	All	Ic	500	mA
Power Dissipation	(Note 1)	P_d	200	mW
Thermal Resistance, Junction to Ambient Air	(Note 1)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Notes:

- Mounted on FR4 PC Board with recommended pad layout at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.



Electrical Characteristics @TA = 25°C unless otherwise specified R1, R2 Types

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition				
Input Voltage	DDTD122LU DDTD142JU	V _{I(off)}	0.3 0.3	_	_	٧	V _{CC} = 5V, I _O = 100μA			
	DDTD122LU DDTD142JU	$V_{I(on)}$		_	2.0 2.0	٧	$V_O = 0.3V$, $I_O = 20mA$ $V_O = 0.3V$, $I_O = 20mA$			
Output Voltage		$V_{O(on)}$		_	0.3V	V	$I_O/I_I = 50 \text{mA}/2.5 \text{mA}$			
Input Current DDTD122LU DDTD142JU		lı		_	28 13	mA	V _I = 5V			
Output Current		I _{O(off)}		_	0.5	μА	$V_{CC} = 50V$, $V_I = 0V$			
DC Current Gain DDTD122LU DDTD142JU		Gı	56 56	_			V _O = 5V, I _O = 50mA			
Gain-Bandwidth Product*		f _T	_	200	_	MHz	$V_{CE} = 10V, I_{E} = 5mA, f = 100MHz$			

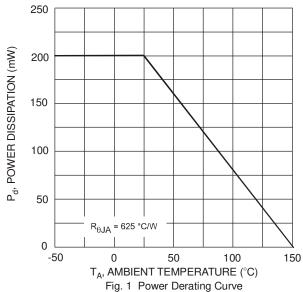
^{*} Transistor - For Reference Only

Electrical Characteristics @T_A = 25°C unless otherwise specified R1-Only, R2-Only Types

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	_	٧	I _C = 50μA	
Collector-Emitter Breakdown Voltage	BV _{CEO}	40	_	_	٧	I _C = 1mA	
Emitter-Base Breakdown Voltage DDTD122TU DDTD142TU		BV _{EBO}	5	_	_	٧	$I_E = 50\mu A$ $I_E = 50\mu A$
Collector Cutoff Current		I _{CBO}	_	_	0.5	μА	V _{CB} = 50V
Emitter Cutoff Current DDTD122TU DDTD142TU		I _{EBO}	_	_	0.5 0.5	μА	V _{EB} = 4V
Collector-Emitter Saturation Voltage		V _{CE(sat)}	_	_	0.3	٧	I _C = 50mA, I _B = 2.5mA
DC Current Transfer Ratio DDTD122TU DDTD142TU		h _{FE}	100 100	250 250	600 600	_	$I_C = 5mA$, $V_{CE} = 5V$
Gain-Bandwidth Product*		f _T	—	200	_	MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz

^{*} Transistor - For Reference Only



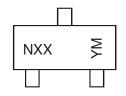


Ordering Information (Note 4 & 5)

Device	Packaging	Shipping
DDTD122LU-7-F	SOT-323	3000/Tape & Reel
DDTD142JU-7-F	SOT-323	3000/Tape & Reel
DDTD122TU-7-F	SOT-323	3000/Tape & Reel
DDTD142TU-7-F	SOT-323	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



NXX = Product Type Marking Code See Page 1 Table

YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	N	Р	R	S	Т	U	V	W	Х	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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